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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)		<b>Complete if Known</b>			
		Application Number	10/671,233-Conf. #8199		
		Filing Date	September 25, 2003		
		First Named Inventor	Jian H. Zhao		
		Art Unit	2826		
		Examiner Name	T. N. Tran		
Sheet	1	of	1	Attorney Docket Number	OCIRS 3.0-088

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
TT	AA	US-6,107,649	08-22-2000	Jian H. Zhao	Column 1, Figure 6A
TT	AB	US-5,903,020	05-11-99	Richard R. Siergiej, et al.	Fig. 3, Fig. 5, Fig. 10

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>4</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	MM-DD-YYYY			

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NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>2</sup>
TT	CC	K. ASANO, et. al, 5kV 4H-SiC SEJFET with Low RonS of 69 m-ohm-cm2, Proc. of 14 <sup>th</sup> Intl. Symp. on Power Semiconductor Devices & IC 2002, June 3, 2002, pp. 61-64, IEEE, Piscataway, NJ, USA.		
TT	CD	J. Nishizawa, et. al., The 2.45 GHz 35 W CW SI recessed gate type SIT with high gain and high voltage operation, IEEE Trans. on Electron Devices, Feb. 2000, pp. 482-487, Vol. 4, No. 2, IEEE, Piscataway, NJ, USA		
TT	CE	H. Onose, et. al., 2KV 4H-SiC junction FETs, Materials Science Forum, 2002, pp. 1227-1230, Vols. 389-393, Trans Tech Publications, Switzerland		
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TT	CG	Jian H. Zhao, et al., Demonstration of a high performance 4H-SiC vertical junction field effect transistor without epitaxial regrowth, Feb. 2003, pp. 321-323, Electronics Letters, IEE, Stevenage. SG1 2SD. UK.		

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